Markus Pristovsek

List of Publications by Year
in descending order

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135	2,287	218677	330143
papers	citations	26 h-index	37 g-index

135	135	135	1709
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	The critical thickness of InGaN on (0001)GaN. Journal of Crystal Growth, 2008, 310, 4913-4915.	1.5	104
2	Atomic structure of InP(001)-(2Ã—4): A dimer reconstruction. Physical Review B, 1998, 57, 14596-14599.	3.2	64
3	(2Ã—4)GaP(001) surface: Atomic structure and optical anisotropy. Physical Review B, 1999, 60, 2488-2494.	3.2	58
4	Real-time monitoring of MOVPE device growth by reflectance anisotropy spectroscopy and related optical techniques. Journal of Crystal Growth, 1998, 195, 151-162.	1.5	54
5	Insight into the performance of multi-color InGaN/GaN nanorod light emitting diodes. Scientific Reports, 2018, 8, 7311.	3.3	51
6	GaP(001) and InP(001): Reflectance anisotropy and surface geometry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1691.	1.6	50
7	Surface diffusion and layer morphology of ((112Â¯2)) GaN grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	2.5	48
8	Growth of hexagonal boron nitride on sapphire substrate by pulsed-mode metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2018, 482, 1-8.	1.5	46
9	MOVPE growth of semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0007.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>11</mml:mn><mml:mover) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 427 Td (accent="t	1.5	45
10	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0008.gif" overflow="scroll"><mml:mo Reflectance anisotropy oscillations during MOCVD and MBE growth of GaAs (001). Physica Status Solidi A, 1995, 152, 35-47.	1.7	43
11	Surface processes before and during growth of GaAs (001). Journal of Crystal Growth, 1994, 145, 44-52.	1.5	42
12	Orientation control of GaN and grown on sapphire by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 2171-2174.	1.5	42
13	Crystal orientation of GaN layers on (101 0) m -plane sapphire. Physica Status Solidi (B): Basic Research, 2011, 248, 583-587.	1.5	42
14	Growth oscillations with monolayer periodicity monitored by ellipsometry during metalorganic vapor phase epitaxy of GaAs(001). Applied Physics Letters, 1995, 67, 3783-3785.	3.3	41
15	Radiative recombination mechanisms in polar and non-polar InGaN/GaN quantum well LED structures. Applied Physics Letters, 2016, 109, .	3.3	41
16	Structural and optical properties of semipolar AlGaN grown on sapphire by metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 367, 42-47.	1.5	40
17	Scanning-tunneling-microscopy study of InP(001) surfaces prepared by UHV decapping of metal-organic vapor-phase-epitaxy-grown samples. Physical Review B, 1996, 53, R13257-R13259.	3.2	37
18	Spectroscopic process sensors in MOVPE device production. Applied Physics A: Materials Science and Processing, 1999, 68, 309-313.	2.3	32

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19	Effect of heterostructure design on carrier injection and emission characteristics of 295â€‰nm light emitting diodes. Journal of Applied Physics, 2015, 117, .	2.5	32
20	Topography of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0005.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>20</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 7 phase epitaxy. Journal of Crystal Growth, 2012, 356, 70-74.	1.5	31
21	In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere. Journal of Crystal Growth, 1998, 195, 211-216.	1.5	30
22	High aluminium content and high growth rates of AlGaN in a close-coupled showerhead MOVPE reactor. Journal of Crystal Growth, 2011, 315, 229-232.	1.5	30
23	Polarity determination of polar and semipolar (112Â¯2)â€‰InN and GaN layers by valence band photoemission spectroscopy. Journal of Applied Physics, 2013, 114, .	2.5	30
24	Structure analysis of the Ga-stabilizedGaAs(001)â˜c(8Ã—2)surface at high temperatures. Physical Review B, 2002, 65, .	3.2	28
25	Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during AlxGa1â˜xAs growth in MOVPE. Journal of Crystal Growth, 2002, 240, 87-97.	1.5	28
26	Gallium-rich reconstructions on GaAs(001). Physica Status Solidi (B): Basic Research, 2003, 240, 91-98.	1.5	27
27	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. Journal of Applied Physics, 2018, 124, .	2.5	27
28	Growth of strained GaAsSb layers on GaAs (001) by MOVPE. Journal of Crystal Growth, 2005, 276, 347-353.	1.5	26
29	Growth and characterizations of semipolar (112Â¯2) InN. Journal of Applied Physics, 2012, 112, .	2.5	26
30	In situ study of GaAs growth mechanisms using tri-methyl gallium and tri-ethyl gallium precursors in metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2004, 262, 78-83.	1.5	25
31	In situ surface passivation of IIIâ€“V semiconductors in MOVPE by amorphous As and P layers. Journal of Crystal Growth, 1997, 170, 230-236.	1.5	24
32	Ellipsometric and reflectance-anisotropy measurements on rotating samples. Thin Solid Films, 1998, 313-314, 620-624.	1.8	24
33	The stability of graphene and boron nitride for III-nitride epitaxy and post-growth exfoliation. Chemical Science, 2021, 12, 7713-7719.	7.4	24
34	Surface structure of ordered InGaP(001): The(2Ã—4)reconstruction. Physical Review B, 2000, 62, 12601-12604.	3.2	23
35	Single phase <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0012.gif" overflow="scroll"><mml:mo stretchy="false">{</mml:mo><mml:mn>1</mml:mn><mml:mspace width="0.25em" /><mml:mn>1</mml:mn><mml:mspace width="0.25em" /><mml:mover accent="true"><mml:mrow><mml:mn>2</mml:mn></mml:mrow><mml:mrow><mml:mo>Â¯</mml:mo></mml:mrow></mml:mover><mml:mspace width="0.25em" /><mml:mn>2</mml:mn><mml:mo stretchy="false">}</mml:mo></mml:math> GaN on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" al Journal of Crystal Growth, 2011, 331	1.5	23
36	Growth mode of InGaN on GaN (0001) in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S565-S569.	0.8	22

#	Article	IF	Citations
37	Metalorganic vapour phase epitaxial growth on vicinal GaAs (001) surfaces studied by reflectance anisotropy spectroscopy. Physica Status Solidi A, 1995, 152, 49-59.	1.7	21
38	In situ investigation of GaAs (001) intrinsic carbon p-doping in metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2000, 221, 149-155.	1.5	21
39	In-situ Determination of the Carrier Concentration of (001) GaAs by Reflectance Anisotropy Spectroscopy. Physica Status Solidi A, 2001, 188, 1423-1429.	1.7	21
40	Indium incorporation efficiency and critical layer thickness of (202Â¯1) InGaN layers on GaN. Applied Physics Letters, 2012, 101, .	3.3	21
41	Efficiency of arsenic and phosphorus precursors investigated by reflectance anisotropy spectroscopy. Journal of Crystal Growth, 1994, 145, 36-43.	1.5	19
42	In situaccess to the dielectric anisotropy of buried III-V/Si(100) heterointerfaces. Physical Review B, 2012, 86, .	3.2	19
43	Growth mode transition and relaxation of thin InGaN layers on GaN (0001). Journal of Crystal Growth, 2013, 372, 65-72.	1.5	19
44	Optimizing GaN () heteroâ€epitaxial templates grown on () sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 61-66.	1.5	19
45	Monolithic integration of tricolor micro-LEDs and color mixing investigation by analog and digital dimming. Japanese Journal of Applied Physics, 2019, 58, SCCC06.	1.5	19
46	Structure of InP (001) surfaces prepared by decapping and by ion bombardment and annealing. Physical Review B, 1997, 56, R1661-R1663.	3.2	18
47	Volmerâ€Weber growth mode of InN quantum dots on GaN by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S545.	0.8	18
48	High-temperature thermal annealing of nonpolar (1 0<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 327 Td (xmlns:mml="http://www		

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55	Effects of Wavelength and Defect Density on the Efficiency of (In,Ga)N-Based Light-Emitting Diodes. Physical Review Applied, 2017, 7, .	3.8	16
56	How to obtain metal-polar untwinned high-quality (1â€¯0â€¯â”1â€¯3) GaN on m-plane sapphire. Journal of Crystal Growth, 2019, 507, 205-208.	1.5	16
57	Interplay of sidewall damage and light extraction efficiency of micro-LEDs. Optics Letters, 2022, 47, 2250.	3.3	15
58	Reconstructions of the GaAs (113) surface. Journal of Crystal Growth, 1998, 195, 1-5.	1.5	14
59	Dynamic study of the surfaces of (001) gallium arsenide in metal-organic vapor-phase epitaxy during arsenic desorption. Journal of Applied Physics, 2000, 87, 1245-1250.	2.5	14
60	In situ scanning tunneling microscopy of InAs quantum dots on GaAs() during molecular beam epitaxial growth. Surface Science, 2003, 544, 234-240.	1.9	14
61	InN growth and annealing investigations using in-situ spectroscopic ellipsometry. Journal of Crystal Growth, 2004, 272, 87-93.	1.5	14
62	Growth of semipolar (10$ ar 1ar 3 $) InN on m â€plane sapphire using MOVPE. Physica Status Solidi - Rapid Research Letters, 2010, 4, 127-129.	2.4	14
63	Growth mechanism of InGaN quantum dots during metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2011, 334, 40-45.	1.5	14
64	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. Journal of Applied Physics, 2016, 120, .	2.5	14
65	MOVPE growth and high-temperature annealing of (101Â¯0) AlN layers on (101Â¯0) sapphire. Journal of Crystal Growth, 2018, 502, 14-18.	1.5	14
66	Simultaneous Growth of Various InGaN/GaN Coreâ€Shell Microstructures for Color Tunable Device Applications. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800361.	1.8	14
67	Ripening of InAs quantum dots on GaAs (001) investigated with in situ scanning tunneling microscopy in metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 4751-4753.	1.5	13
68	Structural and optical properties of Gd implanted GaN with various crystallographic orientations. Thin Solid Films, 2017, 638, 63-72.	1.8	13
69	Effect of substrate misorientation on the concentration of impurities and surface morphology of an epitaxial GaN layer on N-polar GaN substrate by MOVPE. Journal of Crystal Growth, 2019, 512, 78-83.	1.5	13
70	Epitaxial Combination of Two-Dimensional Hexagonal Boron Nitride with Single-Crystalline Diamond Substrate. ACS Applied Materials & Interfaces, 2020, 12, 46466-46475.	8.0	13
71	Influence of the reconstruction of GaAs (001) on the electro-optical bulk properties. Journal of Crystal Growth, 2003, 248, 254-258.	1.5	12
72	Surface transition induced island formation on thin strained InGaN layers on GaN (0001) in metal-organic vapour phase epitaxy. Journal of Applied Physics, 2011, 110, .	2.5	12

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73	Wavelength limits for InGaN quantum wells on GaN. Applied Physics Letters, 2013, 102, .	3.3	12
74	Aluminium incorporation in polar, semi- and non-polar AlGaN layers: a comparative study of x-ray diffraction and optical properties. Scientific Reports, 2019, 9, 15802.	3.3	12
75	Surface and crystal structure of nitridated sapphire substrates and their effect on polar InN layers. Applied Surface Science, 2014, 307, 461-467.	6.1	11
76	Nonpolar m-plane <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si3.gif" overflow="scroll"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mrow><mml:mi>x</mml:mi layers grown on m-plane sapphire by MOVPE. Journal of Crystal Growth, 2019, 512, 100-104.	1.5	11
77	Indium incorporation and optical properties of polar, semipolar and nonpolar InAlN. Semiconductor Science and Technology, 2020, 35, 035004.	2.0	11
78	Indium nitride quantum dot growth modes in metalorganic vapour phase epitaxy. Journal of Crystal Growth, 2008, 310, 4959-4962.	1.5	10
79	Morphological study of InGaN on GaN substrate by supersaturation. Journal of Crystal Growth, 2019, 508, 58-65.	1.5	10
80	Response of the surface dielectric function to dynamic surface modifications: application of reflectance anisotropy spectroscopy and spectroscopic ellipsometry. Thin Solid Films, 1998, 313-314, 537-543.	1.8	9
81	Comparative study of the GaAs (113), (115), (001), (115) , (113) , and (110) surfaces by atomic force microscopy, low energy electron diffraction, and reflectance anisotropy spectroscopy. Microelectronics Journal, 1999, 30, 449-453.	2.0	9
82	InN growth on sapphire using different nitridation procedures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1622-1625.	1.8	9
83	Pulsed-flow growth of polar, semipolar and nonpolar AlGaN. Journal of Materials Chemistry C, 2020, 8, 8668-8675.	5.5	9
84	Segregation and desorption of antimony in InP (001) in MOVPE. Journal of Crystal Growth, 2007, 298, 159-162.	1.5	8
85	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metalâ€“Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	1.5	8
86	Origin of faceted surface hillocks on semi-polar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0007.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mrow><mml:mn>1</mml:mn><mml:mspace width=".16em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 2 template	1.5	8
87	Deoxidation of (001) IIIâ€“V semiconductors in metal-organic vapour phase epitaxy. Journal of Applied Physics, 2016, 120, 085701.	2.5	8
88	Development of semipolar (11-22) LEDs on GaN templates. Proceedings of SPIE, 2016, , .	0.8	8
89	Ammonia decomposition and reaction by high-resolution mass spectrometry for group III â€“ Nitride epitaxial growth. Journal of Crystal Growth, 2019, 516, 63-66.	1.5	8
90	Atomic structure and composition of the (2Ã—4) reconstruction of InGaP(001). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2210.	1.6	7

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91	In situ scanning tunnelling microscopy during metal-organic vapour phase epitaxy. Journal of Crystal Growth, 2007, 298, 8-11.	1.5	7
92	Energetics of Quantum Dot Formation and Relaxation of InGaAs on GaAs(001). Japanese Journal of Applied Physics, 2013, 52, 041201.	1.5	7
93	Comparative study of (0001) and $(11ar{2}2)$ InGaN based light emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ10.	1.5	7
94	Surface reconstructions of (0001) AlN during metalâ€•organic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2017, 254, 1600711.	1.5	7
95	Strain-induced yellow to blue emission tailoring of axial InGaN/GaN quantum wells in GaN nanorods synthesized by nanoimprint lithography. Scientific Reports, 2021, 11, 6754.	3.3	7
96	Diffusion of Ga on the GaAs (113) surface in the [11Ì„0] direction during MOVPE growth. Applied Surface Science, 2000, 166, 433-436.	6.1	6
97	In situ scanning tunneling microscopy during metal-organic vapor phase epitaxy. Applied Physics Letters, 2006, 89, 063108.	3.3	6
98	Homoepitaxial growth rate measurement using in situ reflectance anisotropy spectroscopy. Journal of Crystal Growth, 2007, 298, 46-49.	1.5	6
99	Comparison study of Nâ€•and Inâ€•polar {0001} InN layers grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 977-981.	0.8	6
100	Surface Transitions During InGaN Growth on GaN(0001) in Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB23.	1.5	6
101	Structure of Ga-stabilized GaAs(0 0 1) surfaces at high temperatures. Applied Surface Science, 2003, 212-213, 146-150.	6.1	5
102	Role of nitridation on polarity and growth of InN by metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2013, 376, 17-22.	1.5	5
103	Toward defectâ€free semiâ€polar GaN templates on preâ€structured sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 834-839.	1.5	5
104	MOVPE growth and indium incorporation of polar, semipolar (112) and (201)â€‰InGaN. Physica Status Solidi (B): Basic Research, 2016, 253, 93-98.	1.5	5
105	Structural and optical properties of (112Ì…2) InGaN quantum wells compared to (0001) and (112Ì…0). Semiconductor Science and Technology, 2016, 31, 085007.	2.0	5
106	Comparing high-purity c- and m-plane GaN layers for Schottky barrier diodes grown homoepitaxially by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2018, 57, 105501.	1.5	5
107	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. Nanomaterials, 2021, 11, 2396.	4.1	5
108	Defect characterization of {101Â¯3} GaN by electron microscopy. Journal of Applied Physics, 2022, 131, .	2.5	5

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109	Photoluminescence Scanning Near-Field Optical Microscopy on IIIâ€“V Quantum Dots. Physica Status Solidi A, 1998, 170, 401-410.	1.7	4
110	Structural analysis by reflectance anisotropy spectroscopy: As and Sb on GaAs(110). Journal of Physics Condensed Matter, 2004, 16, S4367-S4374.	1.8	4
111	Nitrogenâ€“arsenic exchange processes and investigation of the nitrided GaAs surfaces in MOVPE. Journal of Crystal Growth, 2004, 272, 30-36.	1.5	4
112	Properties of InMnP (001) grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4046-4049.	1.5	4
113	Determination of the complex linear electroâ€optic coefficient of GaAs and InP. Physica Status Solidi (B): Basic Research, 2010, 247, 1974-1978.	1.5	4
114	Influence of group III and group V partial pressures on the size and density of InGaN quantum dots in MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2487-2491.	1.8	4
115	Nucleation and Coalescence of Indium Rich InGaN Layers on Nitridated Sapphire in Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JD03.	1.5	4
116	The impact of the surface on step-bunching and diffusion of Ga on GaAs (001) in metal-organic vapour phase epitaxy. Materials Research Express, 2016, 3, 075902.	1.6	4
117	Untwinned semipolar (101Ì…3) Al_xGa_{1-x}N layers grown on m-plane sapphire. Semiconductor Science and Technology, 2019, 34, 125012.	2.0	4
118	Effect of gas phase temperature on InGaN grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2019, 509, 50-53.	1.5	4
119	X-ray characterisation of the basal stacking fault densities of (112Ì„2) GaN. CrystEngComm, 2021, 23, 6059-6069.	2.6	4
120	Limitation of simple np-n tunnel junction based LEDs grown by metal-organic vapor phase epitaxy. Semiconductor Science and Technology, 2020, 35, 115005.	2.0	4
121	Lateral short range ordering of step bunches in InGaAs/GaAs superlattices. Journal of Applied Physics, 2004, 95, 1736-1739.	2.5	3
122	Development of InN metalorganic vapor phase epitaxy using in-situ spectroscopic ellipsometry. Crystal Research and Technology, 2005, 40, 993-996.	1.3	3
123	Shape of indium nitride quantum dots and nanostructures grown by metal organic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S574-S577.	0.8	3
124	Controlling the orientations of directional sputtered non- and semi-polar GaN/AlN layers. Japanese Journal of Applied Physics, 2019, 58, SC1044.	1.5	3
125	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by Metalâ€“Organic Vapour Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 031004.	1.5	3
126	Wurtzite AlP y N1â^'y : a new III-V compound semiconductor lattice-matched to GaN (0001). Applied Physics Express, 2020, 13, 111001.	2.4	3

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127	In situ study of low-temperature growth and Mn, Si, Sn doping of GaAs () in molecular beam epitaxy. Journal of Crystal Growth, 2004, 265, 425-433. Increasing the Luminescence Efficiency of Long-Wavelength (<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 727 Td (xmlns:mml="ht	1.5	2
128	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow>	3.8	2
129	Metalorganic vapor phase epitaxy of InN on GaN using tertiary-butylhydrazine as nitrogen source. Journal of Crystal Growth, 2010, 312, 1983-1985.	1.5	1
130	Corrigendum to â€œMorphological study of InGaN on GaN substrate by supersaturationâ€•[J. Cryst. Growth 508 (2019) 58â€“65]. Journal of Crystal Growth, 2019, 514, 13.	1.5	1
131	Growth and characterization of manganese-doped InAsP. Journal of Crystal Growth, 2008, 310, 5028-5031.	1.5	0
132	In-Situ Monitoring for Nano-Structure Growth inÂMOVPE. Nanoscience and Technology, 2008, , 67-86.	1.5	0
133	Interface and surface dielectric anisotropies of GaP/Si(100). , 2012, , .		0
134	Breakdown of the green gap in (0001) InGaN LEDs. , 2016, , .		0
135	Toward defectâ€free semiâ€polar GaN templates on preâ€structured sapphire (Phys. Status Solidi B 5/2016). Physica Status Solidi (B): Basic Research, 2016, 253, 1024-1024.	1.5	0